

forming a thin dielectric layer on one of the pair of gate oxides, wherein the thin dielectric layer exhibits resistance to oxidation at high temperatures; and

forming the other of the pair of gate oxides to a second thickness different from the first thickness.

**REMARKS**

Applicant has carefully reviewed and considered the amended final Office Action faxed January 10, 2003, and the references cited therewith.

Claims 33, 55, 62, 67, 73, 78, 82, and 86 are amended, no claims are canceled, and no claims are added; as a result, claims 33-40, and 55-86 are now pending in this application.

A telephonic interview with the Examiner was conducted on February 11, 2003. The Okazawa reference (US Pat. No. 4,700,212) was discussed. It was agreed that Okazawa does not teach dielectric layers of different thicknesses. Applicant respectfully submits that pursuant to discussions in the interview, the claims as amended are in condition for allowance. Reconsideration and withdrawal of pending 35 USC § 102 and 35 USC § 103 rejections is respectfully requested.

Conclusion

Applicant respectfully submits that the claims are in condition for allowance and notification to that effect is earnestly requested. The Examiner is invited to telephone Applicant's attorney (612) 373-6944 to facilitate prosecution of this application.

If necessary, please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
Minneapolis, MN 55402  
(612) 373-6944

Date 2/12/03

By 

David C. Peterson  
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Box AF, Commissioner of Patents, Washington, D.C. 20231, on this 12<sup>th</sup> day of February, 2003

Name

Amy Moriarty

Signature

Amy Moriarty